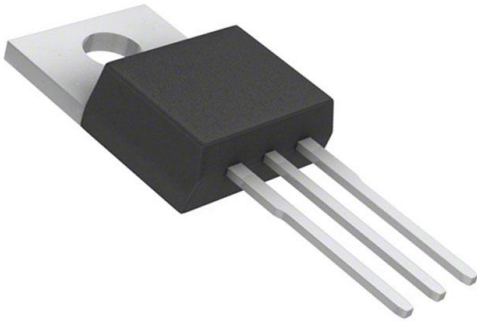


KSE3055T Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	KSE3055T-DG
Manufacturer	onsemi
Manufacturer Product Number	KSE3055T
Description	TRANS NPN 60V 10A TO220-3
Detailed Description	Bipolar (BJT) Transistor NPN 60 V 10 A 2MHz 600 mW Through Hole TO-220-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

KSE3055T

Series:

-

Transistor Type:

NPN

Voltage - Collector Emitter Breakdown (Max):

60 V

Current - Collector Cutoff (Max):

700µA

Power - Max:

600 mW

Operating Temperature:

150°C (TJ)

Package / Case:

TO-220-3

Base Product Number:

KSE30

Manufacturer:

onsemi

Product Status:

Obsolete

Current - Collector (Ic) (Max):

10 A

Vce Saturation (Max) @ Ib, Ic:

8V @ 3.3A, 10A

DC Current Gain (hFE) (Min) @ Ic, Vce:

20 @ 4A, 4V

Frequency - Transition:

2MHz

Mounting Type:

Through Hole

Supplier Device Package:

TO-220-3

Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

REACH Status:

REACH Unaffected

HTSUS:

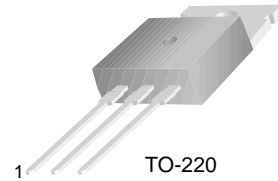
8541.21.0095



KSE3055T

General Purpose and Switching Applications

- DC Current Gain Specified to $I_C = 10A$
- High Current Gain-Bandwidth Product : $f_T = 2MHz$ (Min.)



1.Base 2.Collector 3.Emitter

NPN Silicon Transistor

Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector -Base Voltage	70	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	10	A
I_B	Base Current	6	A
P_C	Collector Dissipation ($T_C = 25^\circ C$)	75	W
	Collector Dissipation ($T_a = 25^\circ C$)	0.6	W
T_J	Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature	- 55 ~ 150	$^\circ C$

Electrical Characteristics $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 200mA, I_B = 0$	60		V
I_{CEO}	Collector Cut-off Current	$V_{CE} = 30V, I_B = 0$		700	μA
I_{CEX1} I_{CEX2}	Collector Cut-off Current	$V_{CE} = 70V, V_{BE}(off) = -1.5V$ $V_{CE} = 70V, V_{BE}(off) = -1.5V$ @ $T_C = 150^\circ C$		1 5	mA mA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_C = 0$		5	mA
h_{FE}	*DC Current Gain	$V_{CE} = 4V, I_C = 4A$ $V_{CE} = 4V, I_C = 10A$	20 5	100	
$V_{CE}(sat)$	*Collector-Emitter Saturation Voltage	$I_C = 4A, I_B = 0.4A$ $I_C = 10A, I_B = 3.3A$		1.1 8	V V
$V_{BE}(on)$	*Base-Emitter On Voltage	$V_{CE} = 4V, I_C = 4A$		1.8	V
f_T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_C = 500mA$	2		MHz

* Pulse test: $PW \leq 300\mu s$, duty cycle $\leq 2\%$ Pulse

Typical Characteristics

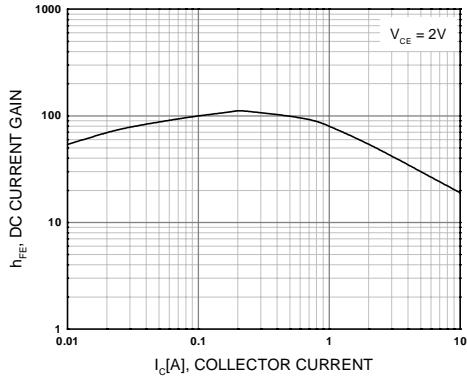


Figure 1. DC current Gain

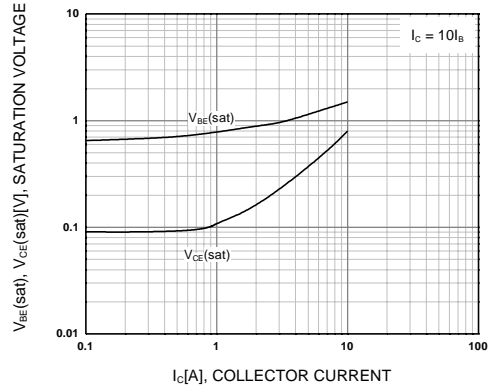


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

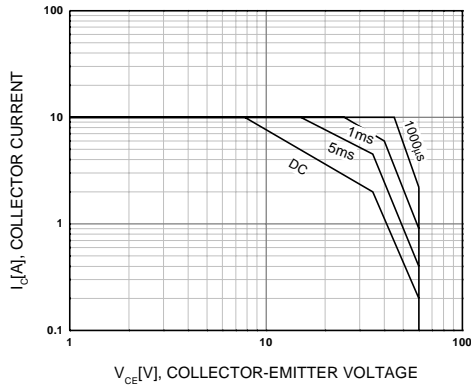


Figure 3. Safe Operating Area

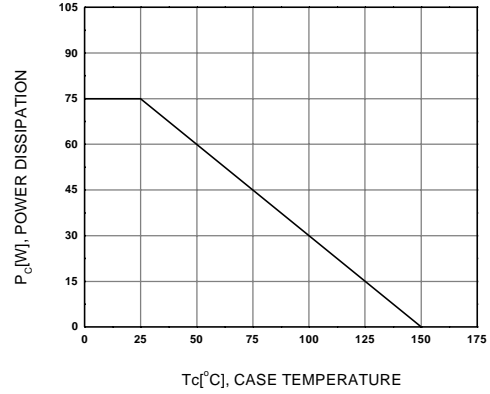
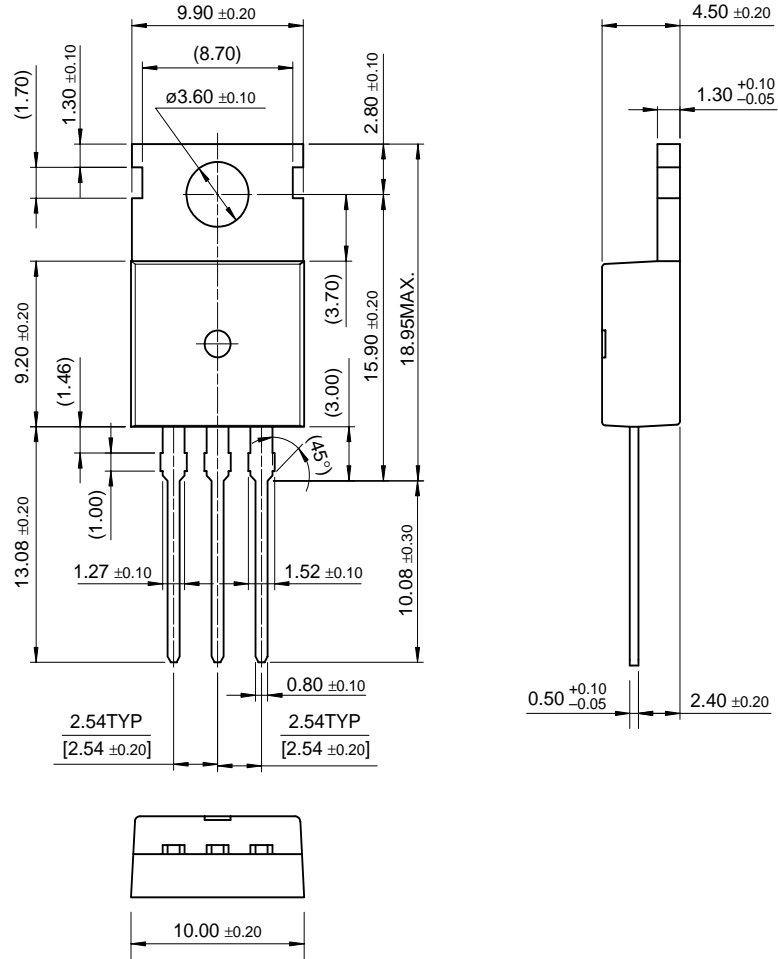


Figure 4. Power Derating

Package Dimensions

TO-220



Dimensions in Millimeters

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	HiSeC™	SuperSOT™-8
Bottomless™	ISOPLANAR™	SyncFET™
CoolFET™	MICROWIRE™	TinyLogic™
CROSSVOLT™	POP™	UHC™
E ² CMOS™	PowerTrench®	VCX™
FACT™	QFET™	
FACT Quiet Series™	QS™	
FAST®	Quiet Series™	
FASTr™	SuperSOT™-3	
GTO™	SuperSOT™-6	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR INTERNATIONAL.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we stricly control the quality of products and services. Welcome your RFQ to

Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.